

MOSFETs Silicon P-Channel MOS (U-MOSVI)

# XPN9R614MC

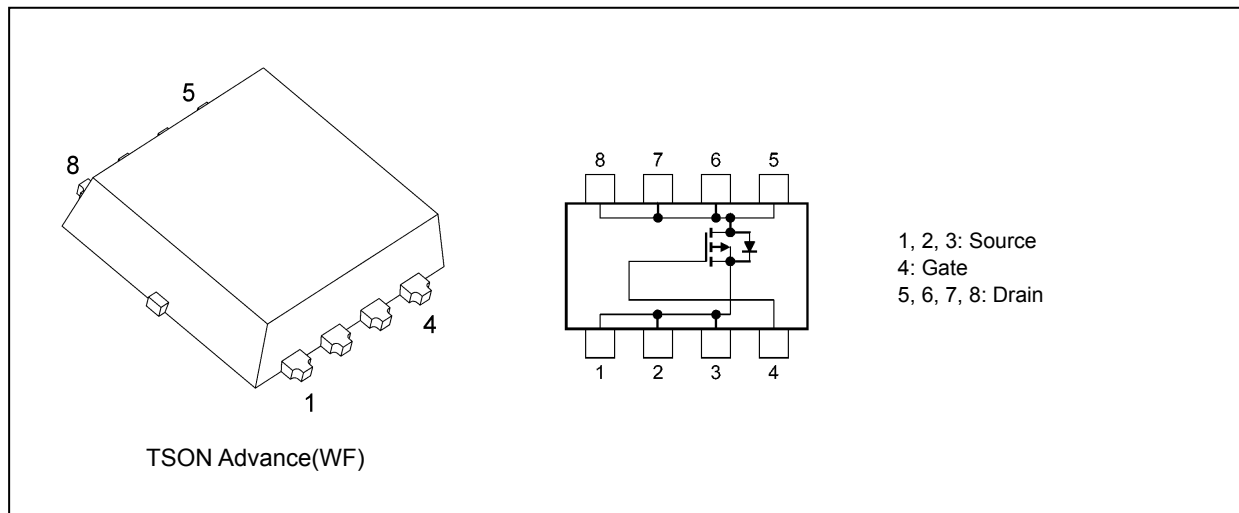
## 1. Applications

- Automotive
- Switching Voltage Regulators
- DC-DC Converters
- Motor Drivers

## 2. Features

- (1) AEC-Q101 qualified
- (2) Small, thin package
- (3) Low drain-source on-resistance:  $R_{DS(ON)} = 7.4 \text{ m}\Omega$  (typ.) ( $V_{GS} = -10 \text{ V}$ )
- (4) Low leakage current:  $I_{DSS} = -10 \text{ }\mu\text{A}$  (max) ( $V_{DS} = -40 \text{ V}$ )
- (5) Enhancement mode:  $V_{th} = -1.0$  to  $-2.1 \text{ V}$  ( $V_{DS} = -10 \text{ V}$ ,  $I_D = -0.5 \text{ mA}$ )

## 3. Packaging and Internal Circuit



Start of commercial production

2018-09

### 4. Absolute Maximum Ratings (Note) ( $T_a = 25\text{ °C}$ unless otherwise specified)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	$V_{DSS}$	-40	V
Gate-source voltage	$V_{GSS}$	+10/-20	
Drain current (DC) (Note 1)	$I_D$	-40	A
Drain current (pulsed) (Note 1)	$I_{DP}$	-80	
Power dissipation ( $T_c = 25\text{ °C}$ )	$P_D$	100	W
Power dissipation ( $t = 10\text{ s}$ ) (Note 2)		2.27	
Power dissipation ( $t = 10\text{ s}$ ) (Note 3)		0.84	
Single-pulse avalanche energy (Note 4)	$E_{AS}$	67	mJ
Single-pulse avalanche current	$I_{AS}$	-40	A
Channel temperature (Note 5)	$T_{ch}$	175	°C
Storage temperature (Note 5)	$T_{stg}$	-55 to 175	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

### 5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal impedance ( $T_c = 25\text{ °C}$ )	$Z_{th(ch-c)}$	1.5	°C/W
Channel-to-ambient thermal impedance ( $t = 10\text{ s}$ ) (Note 2)	$Z_{th(ch-a)}$	66	
Channel-to-ambient thermal impedance ( $t = 10\text{ s}$ ) (Note 3)	$Z_{th(ch-a)}$	178	

Note 1: Ensure that the channel temperature does not exceed 175 °C.

Note 2: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 3: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 4:  $V_{DD} = -25\text{ V}$ ,  $T_{ch} = 25\text{ °C}$  (initial),  $L = 43\text{ }\mu\text{H}$ ,  $R_G = 25\text{ }\Omega$ ,  $I_{AS} = -40\text{ A}$ ,  $V_{GS} = 0/-15\text{ V}$

Note 5: The definitions of the absolute maximum channel and storage temperatures are qualified per AEC-Q101.

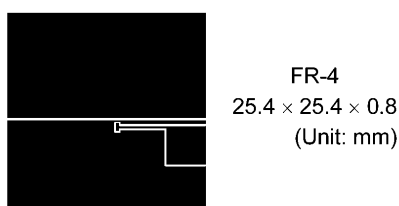


Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)

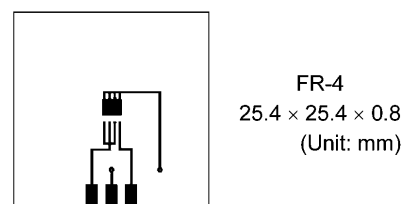


Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

### 6. Electrical Characteristics

#### 6.1. Static Characteristics ( $T_a = 25\text{ }^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	$I_{GSS}$	$V_{GS} = +10/-20\text{ V}, V_{DS} = 0\text{ V}$	—	—	$\pm 1$	$\mu\text{A}$
Drain cut-off current	$I_{DSS}$	$V_{DS} = -40\text{ V}, V_{GS} = 0\text{ V}$	—	—	-10	
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D = -10\text{ mA}, V_{GS} = 0\text{ V}$	-40	—	—	V
	$V_{(BR)DSX}$	$I_D = -10\text{ mA}, V_{GS} = 10\text{ V}$	-30	—	—	
Gate threshold voltage	$V_{th}$	$V_{DS} = -10\text{ V}, I_D = -0.5\text{ mA}$	-1.0	—	-2.1	
Drain-source on-resistance	$R_{DS(ON)}$	$V_{GS} = -4.5\text{ V}, I_D = -20\text{ A}$	—	9.6	13.4	$\text{m}\Omega$
		$V_{GS} = -10\text{ V}, I_D = -20\text{ A}$	—	7.4	9.6	

#### 6.2. Dynamic Characteristics ( $T_a = 25\text{ }^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Input capacitance	$C_{iss}$	$V_{DS} = -10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	3000	—	$\text{pF}$
Reverse transfer capacitance	$C_{rss}$		—	335	—	
Output capacitance	$C_{oss}$		—	410	—	
Gate resistance	$r_g$		—	13	—	
Switching time (rise time)	$t_r$	See Fig. 6.2.1	—	35	—	ns
Switching time (turn-on time)	$t_{on}$		—	50	—	
Switching time (fall time)	$t_f$		—	165	—	
Switching time (turn-off time)	$t_{off}$		—	570	—	

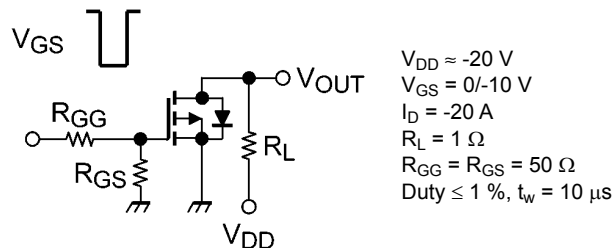


Fig. 6.2.1 Switching Time Test Circuit

#### 6.3. Gate Charge Characteristics ( $T_a = 25\text{ }^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Total gate charge (gate-source plus gate-drain)	$Q_g$	$V_{DD} \approx -32\text{ V}, V_{GS} = -10\text{ V}, I_D = -40\text{ A}$	—	64	—	nC
Gate-source charge 1	$Q_{gs1}$		—	8	—	
Gate-drain charge	$Q_{gd}$		—	17	—	

#### 6.4. Source-Drain Characteristics ( $T_a = 25\text{ }^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Reverse drain current (DC) (Note 6)	$I_{DR}$	—	—	—	-40	A
Reverse drain current (pulsed) (Note 6)	$I_{DRP}$	—	—	—	-80	A
Diode forward voltage	$V_{DSF}$	$I_{DR} = -40\text{ A}, V_{GS} = 0\text{ V}$	—	—	1.2	V

Note 6: Ensure that the channel temperature does not exceed  $175\text{ }^\circ\text{C}$ .

## 7. Marking

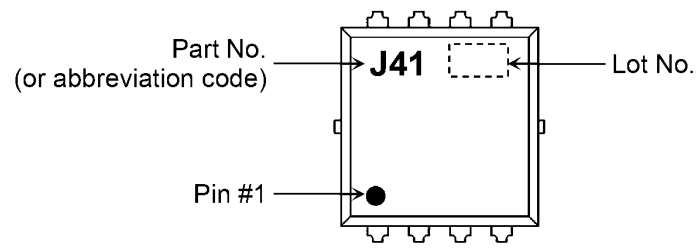
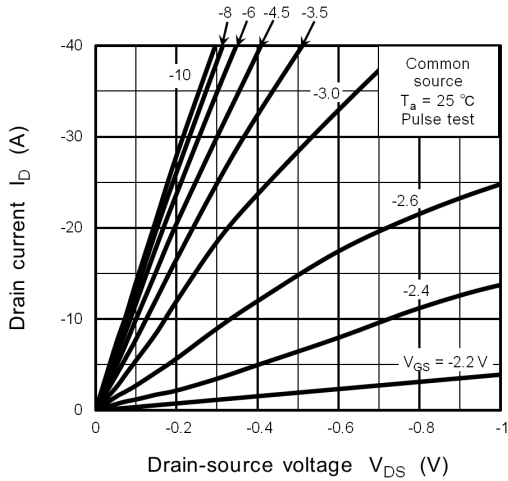
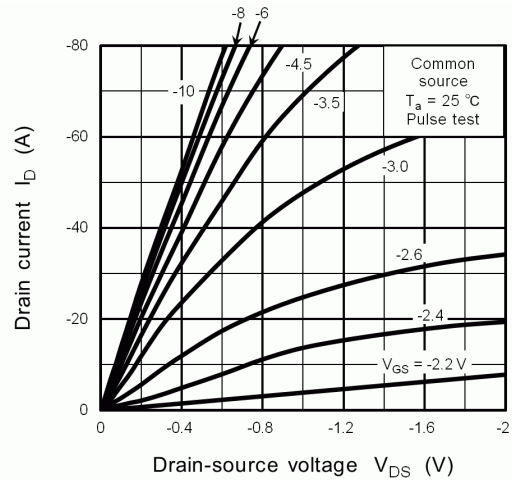


Fig. 7.1 Marking

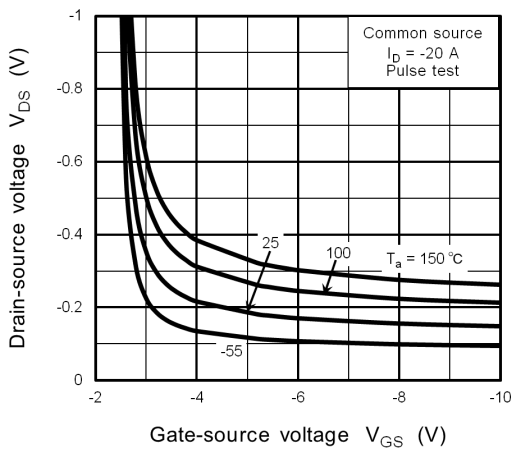
### 8. Characteristics Curves (Note)



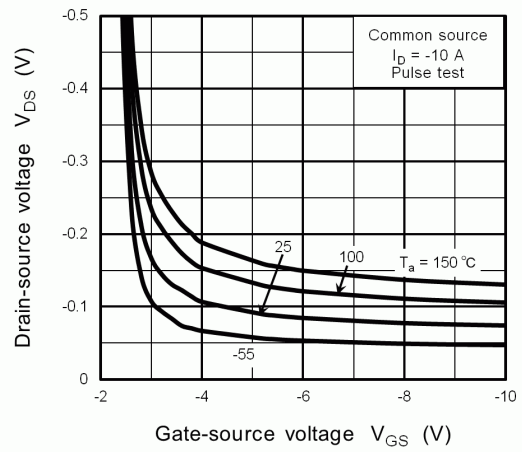
**Fig. 8.1  $I_D - V_{DS}$**



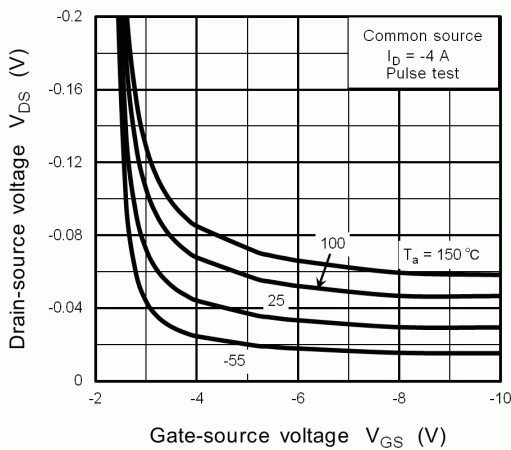
**Fig. 8.2  $I_D - V_{DS}$**



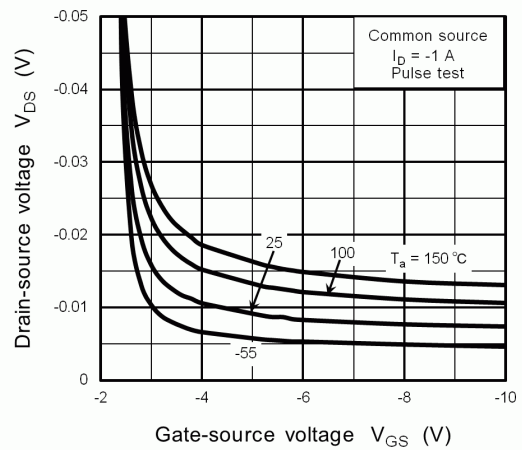
**Fig. 8.3  $V_{DS} - V_{GS}$**



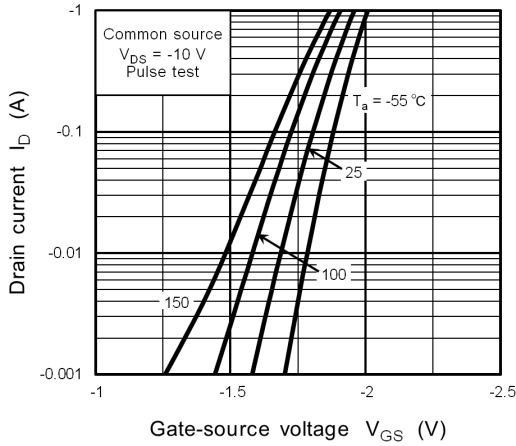
**Fig. 8.4  $V_{DS} - V_{GS}$**



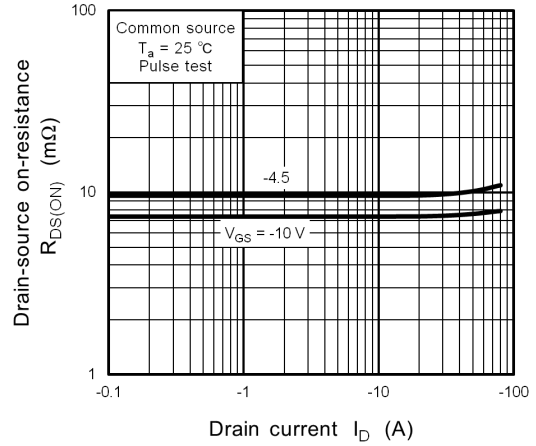
**Fig. 8.5  $V_{DS} - V_{GS}$**



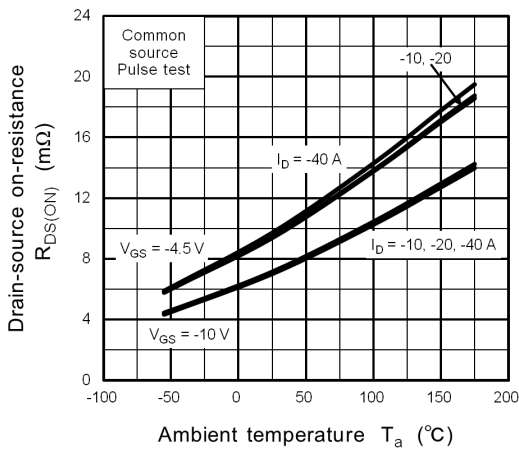
**Fig. 8.6  $V_{DS} - V_{GS}$**



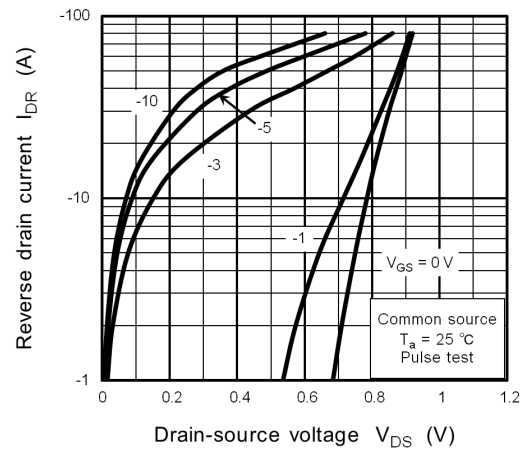
**Fig. 8.7  $I_D - V_{GS}$**



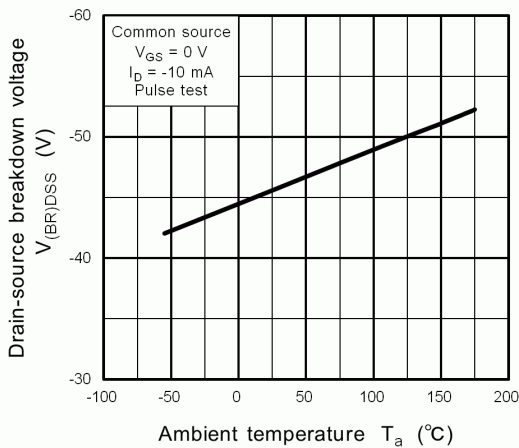
**Fig. 8.8  $R_{DS(ON)} - I_D$**



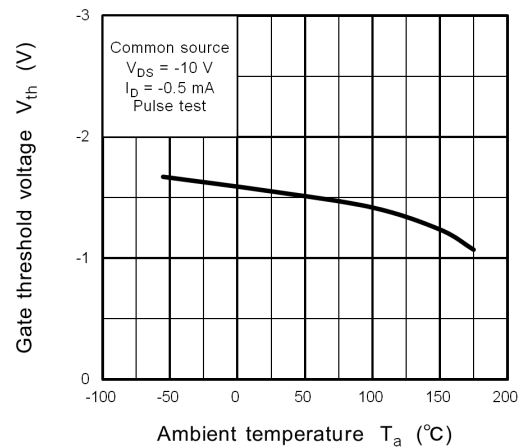
**Fig. 8.9  $R_{DS(ON)} - T_a$**



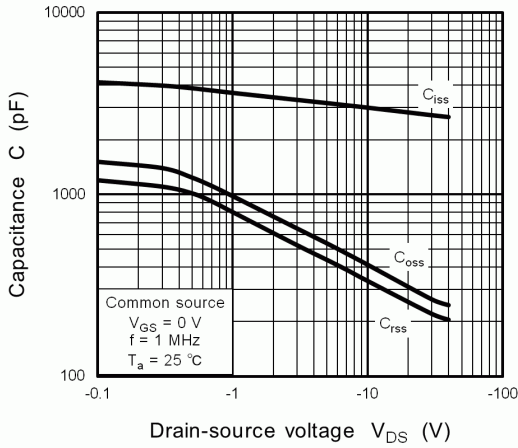
**Fig. 8.10  $I_{DR} - V_{DS}$**



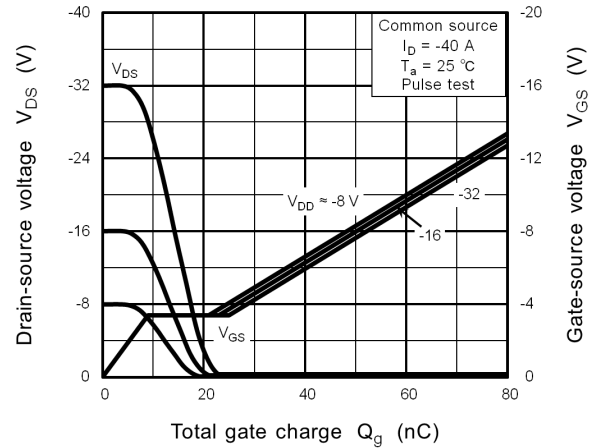
**Fig. 8.11  $V_{(BR)DSS} - T_a$**



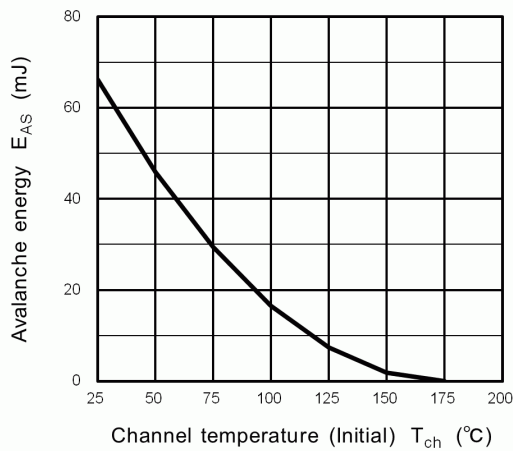
**Fig. 8.12  $V_{th} - T_a$**



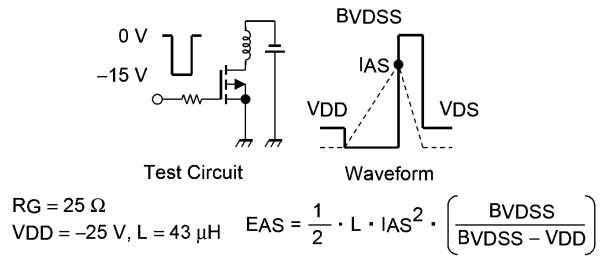
**Fig. 8.13 Capacitance -  $V_{DS}$**



**Fig. 8.14 Dynamic Input/Output Characteristics**

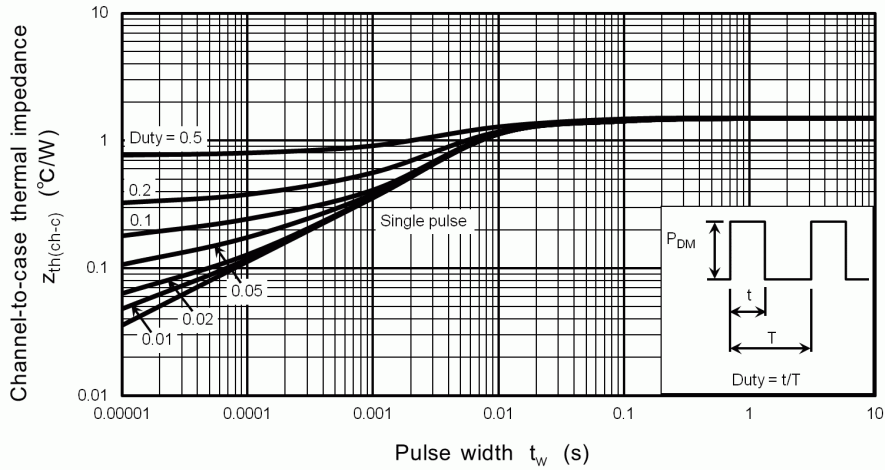


**Fig. 8.15  $E_{AS}$  -  $T_{ch}$**

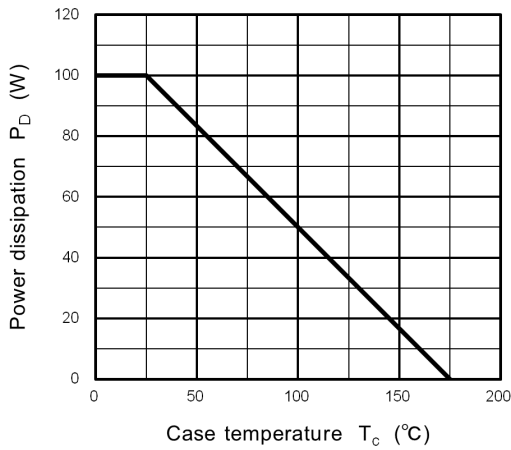


**Fig. 8.16 Test Circuit/Waveform**

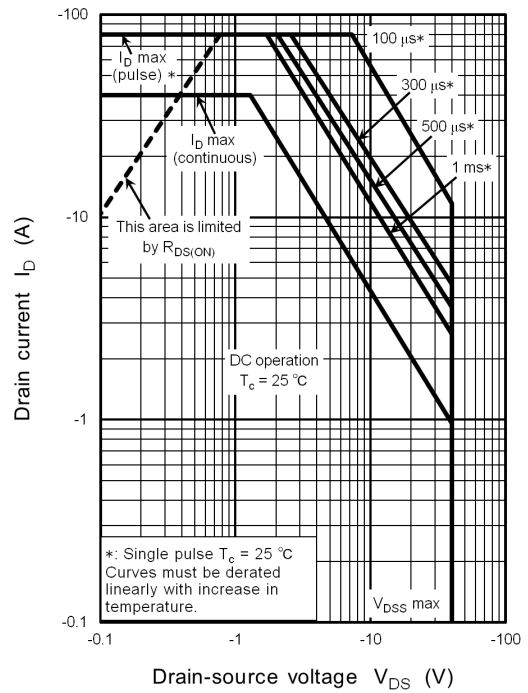
$$E_{AS} = \frac{1}{2} \cdot L \cdot I_{AS}^2 \cdot \left( \frac{BVDSS}{BVDSS - V_{DD}} \right)$$



**Fig. 8.17  $Z_{th(ch-c)} - t_w$   
(Guaranteed Maximum)**



**Fig. 8.18  $P_D - T_c$   
(Guaranteed Maximum)**



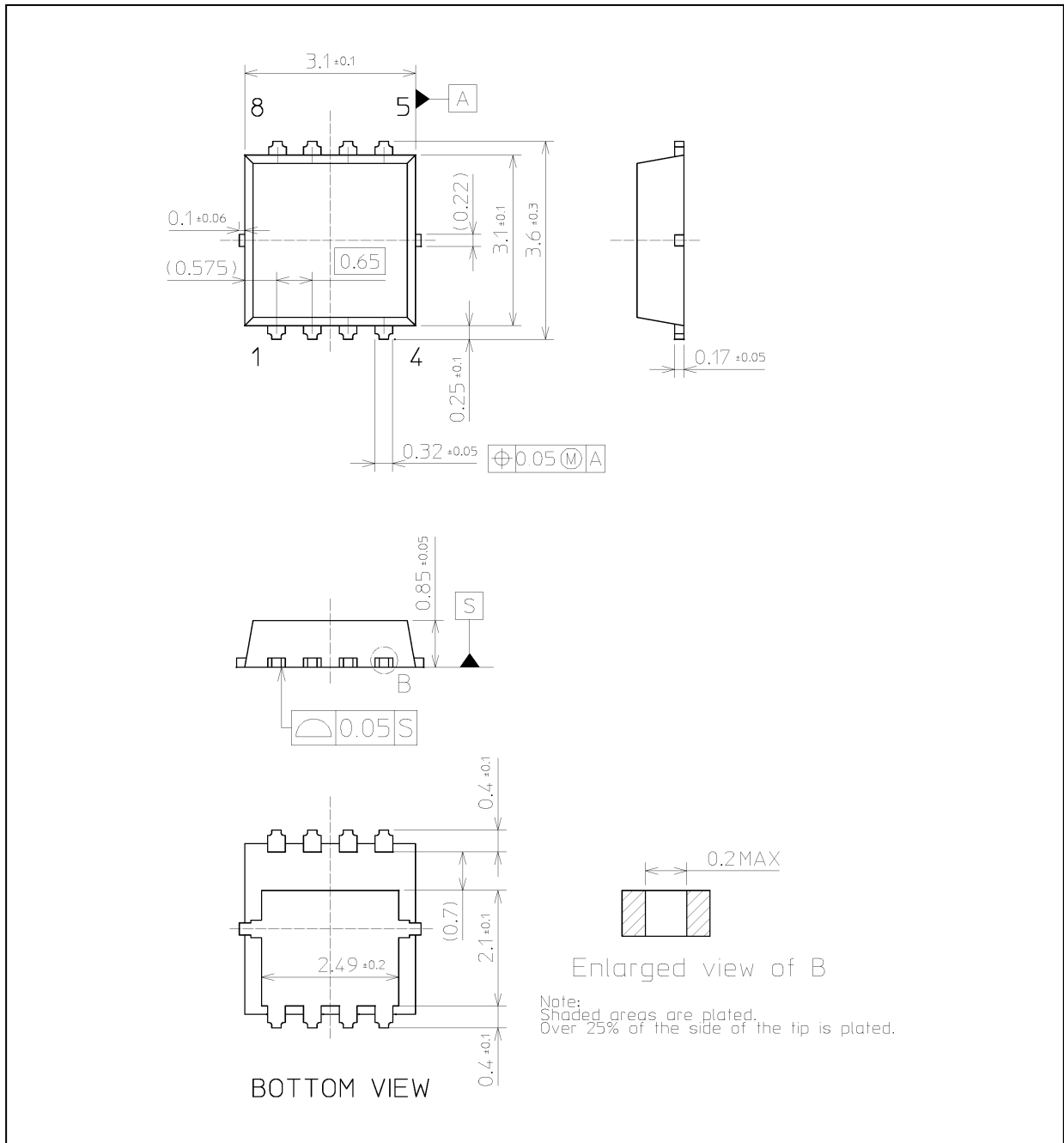
**Fig. 8.19 Safe Operating Area  
(Guaranteed Maximum)**

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



### Package Dimensions

Unit: mm



Weight: 0.029 g (typ.)

Package Name(s)
TOSHIBA: 2-3X2A
Nickname: TSON Advance(WF)

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